L Number	Hits	Search Text	DB	Time stamp
14	3305	(silicidation or silicide or sin or	USPAT;	2003/11/29 19:20
!		(silicon near3 nitride)) and (inductor\$1	US-PGPUB;	
		or (spiral near3 conductor))	EPO; JPO;	
ļ			DERWENT;	
			IBM_TDB	
15	353	(silicidation or silicide or sin or	USPAT;	2003/11/29 20:09
		(silicon near3 nítride)) SAME	US-PGPUB;	
		(inductor\$1 or (spiral near3 conductor))	EPO; JPO; DERWENT;	
	!		IBM TDB	
16	1547	257/532.ccls.	USPAT;	2003/11/29 19:40
10	1047	2377332.0013.	US-PGPUB;	2003/11/23 13:40
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
17	486	257/531.ccls.	USPAT;	2003/11/29 21:08
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
18	243	257/534.ccls.	USPAT;	2003/11/29 19:40
İ	1		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
10	1.05	057/505	IBM_TDB	0000/11/00 10 10
19	165	257/535.ccls.	USPAT;	2003/11/29 19:40
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
20	346	257/621.ccls.	USPAT:	2003/11/29 19:41
20	010	20,7,021.0010.	US-PGPUB;	2000, 11, 23 13.11
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
21	2543	257/532.ccls. or 257/531.ccls. or	USPAT;	2003/11/29 19:41
		257/534.ccls. or 257/535.ccls. or	US-PGPUB;	
		257/621.ccls.	EPO; JPO;	i
			DERWENT;	
22	277	(257/532.ccls. or 257/531.ccls. or	IBM_TDB	0000/11/00 10 10
22	377	257/534.ccls. or 257/535.ccls. or	USPAT; US-PGPUB;	2003/11/29 19:42
		257/621.ccls.) and (inductor or (spiral	EPO; JPO;	ļ
		near3 conductor))	DERWENT;	i
ľ		1.5025 Conductor/	IBM TDB	
23	328	((257/532.ccls. or 257/531.ccls. or	USPAT;	2003/11/29 19:42
		257/534.ccls. or 257/535.ccls. or	US-PGPUB;	1 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2
		257/621.ccls.) and (inductor or (spiral	EPO; JPO;	
		near3 conductor))) not ((silicidation or	DERWENT;	
		silicide or sin or (silicon near3	IBM_TDB	
		nitride)) SAME (inductor\$1 or (spiral		
	_	near3 conductor)))		
24	5	(protrution or protruding near5 substrate)	USPAT;	2003/11/29 20:10
		SAME (inductor\$1 or (spiral near3	US-PGPUB;	
		conductor))	EPO; JPO;	
			DERWENT;	
25	5	((protrution or protruding) near5	IBM_TDB USPAT;	2003/11/29 20:10
23		substrate) SAME (inductor\$1 or (spiral	US-PGPUB;	2003/11/23 20.10
	1	near3 conductor))	EPO; JPO;	
			DERWENT;	
			IBM TDB	
26	315	257/528.ccls.	USPAT;	2003/11/29 21:16
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	L		IBM_TDB	i

		L (20 /200	110000	0000/11/00 01 10
27	113	438/329.ccls.	USPAT;	2003/11/29 21:16
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	1
_	623	257/532.ccls.	USPAT	2003/11/29 19:40
-	1428	silicidation	USPAT	2002/08/06 21:27
_	6	silicidation and inductor\$1	USPAT	2003/07/25 01:56
_	2	silicide adj prevention	USPAT	2002/08/07 15:00
_	209		USPAT	2003/11/29 19:40
_	31		USPAT	2002/08/07 15:15
_	209	7	USPAT	2002/08/07 16:50
1_	623	1 '	USPAT	2002/08/07 16:50
_	111		USPAT	2003/11/29 19:40
	114		USPAT	2003/11/29 19:40
-	123		I .	1
-			USPAT	2002/08/07 16:51
-	0	,,,,	USPAT	2002/08/07 16:51
		257/534.ccls. and 257/535.ccls. and		
		257/621.ccls.		1
-	1035		USPAT	2002/08/07 16:52
1		257/534.ccls. or 257/535.ccls. or		
!		257/621.ccls.		
-	33		USPAT	2002/08/07 16:52
		257/534.ccls. or 257/535.ccls. or		1
1	Í	257/621.ccls.) and doped adj substrate		
-	40	inductor and (doped adj substrate)	USPAT	2002/08/07 17:19
-	410	(silicidation or silicide) and inductor\$1	USPAT;	2003/11/29 19:19
			US-PGPUB;	
			EPO; JPO;	
1			DERWENT:	
	ļ		IBM TDB	
_	261	257/531.ccls.	USPAT	2003/07/25 02:43
_	1489		USPAT;	2003/07/25 02:44
ļ		24.7,462.6628.	US-PGPUB;	2000,01,20 02.41
1			EPO; JPO;	
	1		DERWENT;	
1			IBM TDB	į
! 	442	257/531.ccls.	USPAT;	2003/07/25 02:44
	442	2377331.0013.	1	2003/07/23 02:44
1			US-PGPUB;	
			EPO; JPO;	1
			DERWENT;	
	227	257/53/ 0010	IBM_TDB	0000/07/07 00
-	237	257/534.ccls.	USPAT;	2003/07/25 02:44
į.			US-PGPUB;	
			EPO; JPO;	[
			DERWENT;	
1		055/505	IBM_TDB	
-	153	257/535.ccls.	USPAT;	2003/07/25 02:44
			US-PGPUB;	{
1	1		EPO; JPO;	
			DERWENT;	
)			IBM_TDB	
-	333	257/621.ccls.	USPĀT;	2003/07/25 02:44
			US-PGPUB;	
ļ			EPO; JPO;	1
			DERWENT;	
			IBM TDB	
				L